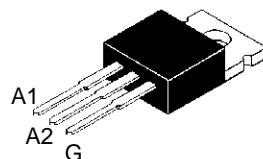


SENSITIVE GATE TRIACS

FEATURES

- $I_T(\text{RMS}) = 8\text{A}$
- $V_{\text{DRM}} = 400\text{V}$ to 800V
- $I_{\text{GT}} \leq 5\text{mA}$ to $\leq 10\text{mA}$



TO220
non-insulated
 (Plastic)

DESCRIPTION

The T08xxxH series of triacs uses a high performance MESA GLASS technology. These parts are intended for general purpose applications where gate high sensitivity is required.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_T(\text{RMS})$	RMS on-state current (360° conduction angle)	95 °C	8
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	$tp = 8.3\text{ ms}$	73
		$tp = 10\text{ ms}$	70
I^2t	I^2t Value for fusing	$tp = 10\text{ ms}$	$A^2\text{s}$
dI/dt	Critical rate of rise of on-state current $I_G = 50\text{ mA}$ $dI_G/dt = 0.1\text{ A}/\mu\text{s}$.	Repetitive $F = 50\text{ Hz}$	10
		Non Repetitive	50
T_{stg} T_j	Storage and operating junction temperature range	- 40, + 150 - 40, + 125	°C
T_l	Maximum lead temperature for soldering during 10s at 4.5mm from case	260	°C

Symbol	Parameter	Voltage				Unit
		D	M	S	N	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ\text{C}$	400	600	700	800	V

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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient	60	°C/W
R _{th(j-c)}	Junction to case for D.C	4	°C/W
R _{th(j-c)}	Junction to case for A.C 360° conduction angle (F=50Hz)	3	°C/W

GATE CHARACTERISTICS (maximum values)

P_{G (AV)}= 1 W P_{GM} = 10 W (tp = 20 µs) I_{GM} = 4 A (tp = 20 µs)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Quadrant		Sensitivity		Unit
				05	09	
I _{GT}	V _D =12V (DC) R _L =33Ω	T _j = 25°C	I-II-III-IV	MAX	5	10 mA
V _{GT}	V _D =12V (DC) R _L =33Ω	T _j = 25°C	I-II-III-IV	MAX	1.5	V
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ	T _j = 125°C	I-II-III-IV	MIN	0.2	V
tgt	V _D =V _{DRM} I _G = 40mA I _T = 11A dI _G /dt = 0.5A/µs	T _j = 25°C	I-II-III-IV	TYP	2	µs
I _H *	I _T = 50mA Gate open	T _j = 25°C		MAX	5	10 mA
I _L	I _G = 1.2 I _{GT}	T _j = 25°C	I-III-IV	TYP	5	10 mA
			II	TYP	10	20
V _{TM} *	ITM= 11A tp= 380µs	T _j = 25°C		MAX	1.65	V
I _{DRM} I _{RRM}	V _D = V _{DRM} V _R = V _{RRM}	T _j = 25°C		MAX	5	µA
		T _j = 110°C		MAX	2	mA
dV/dt *	VD=67%V _{DRM} Gate open	T _j = 110°C		MIN		20 V/µs
				TYP	10	
(dV/dt)c *	(dI/dt)c = 3.5 A/ms	T _j = 110°C		TYP	1	2 V/µs

* For either polarity of electrode A₂ voltage with reference to electrode A₁

ORDERING INFORMATION

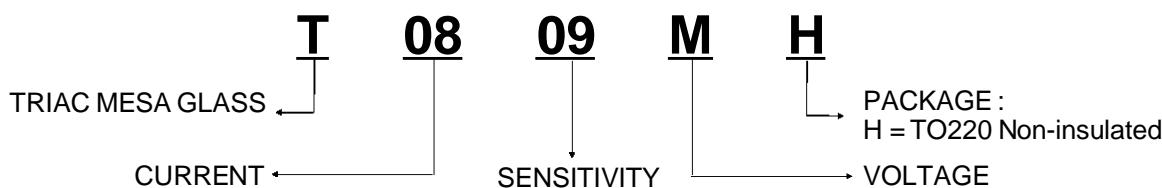


Fig.1 : Maximum RMS power dissipation versus RMS on-state current.

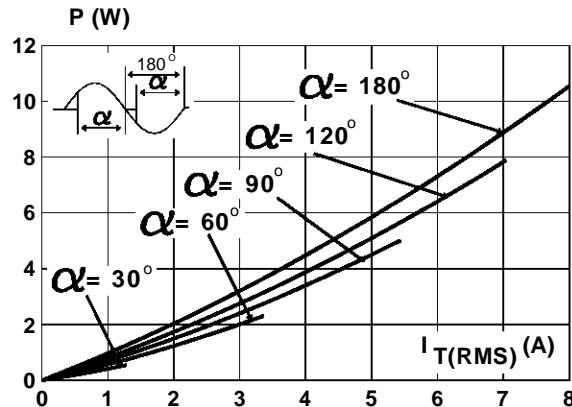


Fig.3 : RMS on-state current versus case temperature.

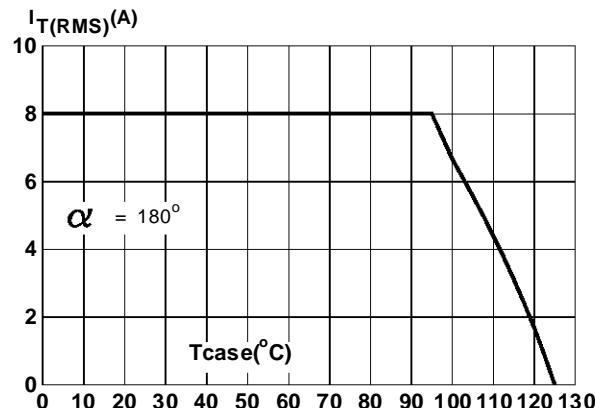


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

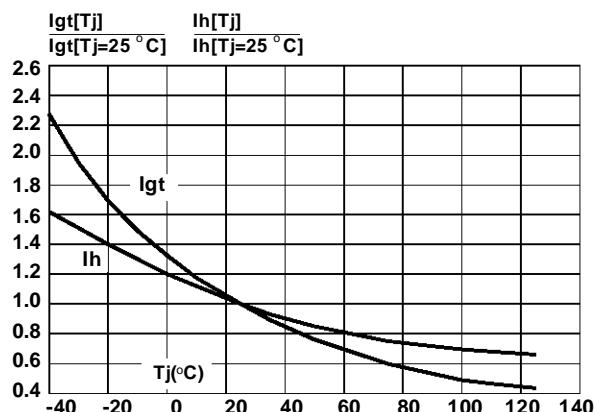


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperature (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

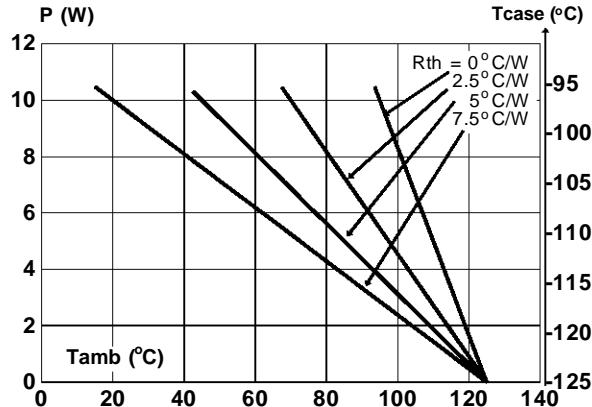


Fig.4 : Relative variation of thermal impedance versus pulse duration.

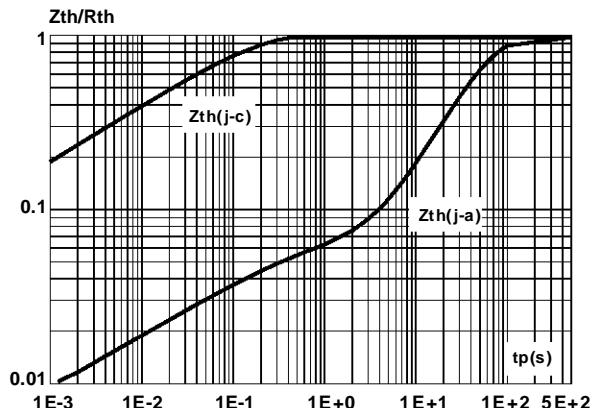
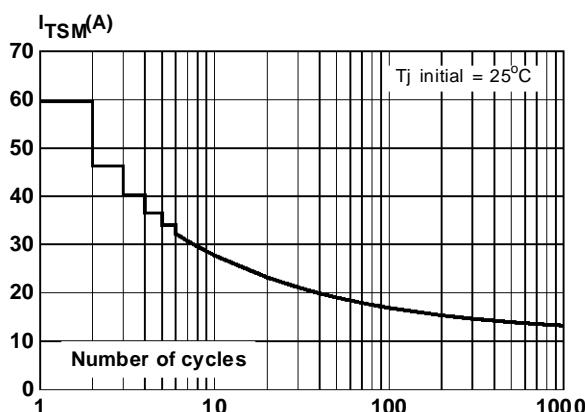


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.



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Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .

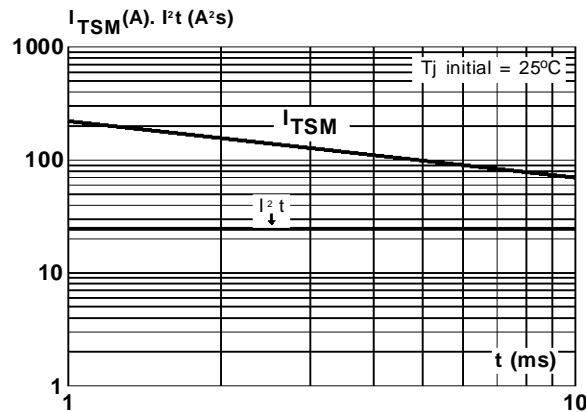
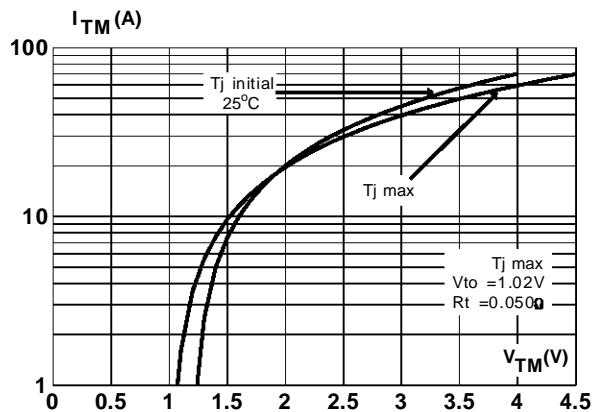


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA
TO220 Non-insulated (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A			10.3			0.406
B	6.3	6.5	0.248	0.256		
C			9.1			0.358
D	12.7				0.500	
F			4.2			0.165
G			3.0			0.118
H	4.5	4.7		0.177	0.185	
I	3.53	3.66		0.139	0.144	
J	1.2	1.3		0.047	0.051	
L			0.9			0.035
M	2.7			0.106		
N			5.3			0.209
N1	2.54			0.100		
O	1.2	1.4		0.047	0.055	
P			1.15			0.045

Marking : type number

Weight : 1.8 g

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